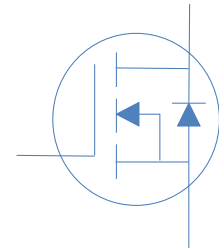


**65V N-Ch Power MOSFET**

$V_{DS}$	65	V
$R_{DS(on),typ}$	2.6	m
$I_D$ (Silicon Limited)	160	A
$I_D$ (Package Limited)	120	A

Part Number	Package	Marking
HGD028NE6A	TO-252	GD028NE6A


**Absolute Maximum Ratings at  $T_J=25^{\circ}\text{C}$  (unless otherwise specified)**

Parameter	Symbol	Conditions	Value	Unit
Continuous Drain Current (Silicon Limited)	$I_D$	$T_C=25^{\circ}\text{C}$	160	A
		$T_C=100^{\circ}\text{C}$	113	
Continuous Drain Current (Package Limited)		$T_C=25^{\circ}\text{C}$	120	
Drain to Source Voltage	$V_{DS}$	-	65	V
Gate to Source Voltage	$V_{GS}$	-	$\pm 20$	V
Pulsed Drain Current	$I_{DM}$	-	400	A
Avalanche Energy, Single Pulse	$E_{AS}$	$L=0.1\text{mH}, T_C=25^{\circ}\text{C}$	80	mJ
Power Dissipation	$P_D$	$T_C=25^{\circ}\text{C}$	150	W
Operating and Storage Temperature	$T_J, T_{stg}$	-	-55 to 175	$^{\circ}\text{C}$

**Absolute Maximum Ratings**

Parameter	Symbol	Max	Unit
Thermal Resistance Junction-Ambient	$R_{JA}$	46	$^{\circ}\text{C/W}$
Thermal Resistance Junction-Case	$R_{JC}$	1	$^{\circ}\text{C/W}$



Total Gate Charge			-		
Gate to Source Charge	$Q_{gs}$	$V_{DD}=30V, I_D=20A, V_{GS}=10V$		16	-
Gate to Drain (Miller) Charge			-	15	-
		$V_{DD}=30V, I_D=20A, V_{GS}=10V,$		12	-
		$R_G=10 \text{ } \Omega$		52	-
				19	-
					ns

### Reverse Diode Characteristics

Diode Forward Voltage	$V_{SD}$	$V_{GS}=0V, I_F=20A$	-	0.9	1.2	V
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Fig 1. Typical Output Characteristics

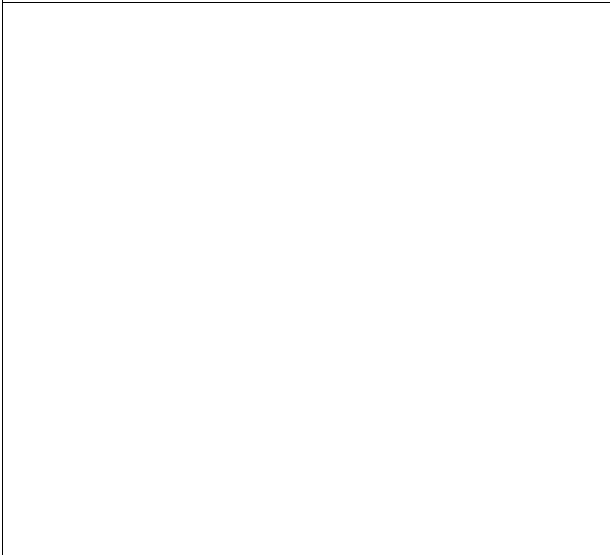


Figure 2. On-Resistance vs. Gate-Source Voltage

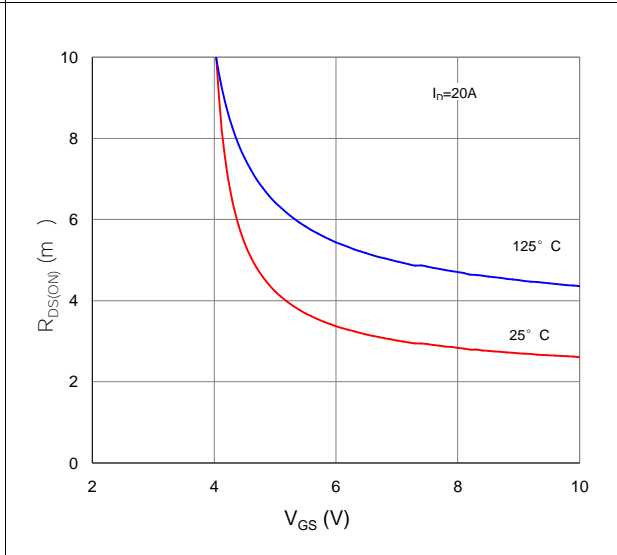


Figure 3. On-Resistance vs. Drain Current and Gate Voltage

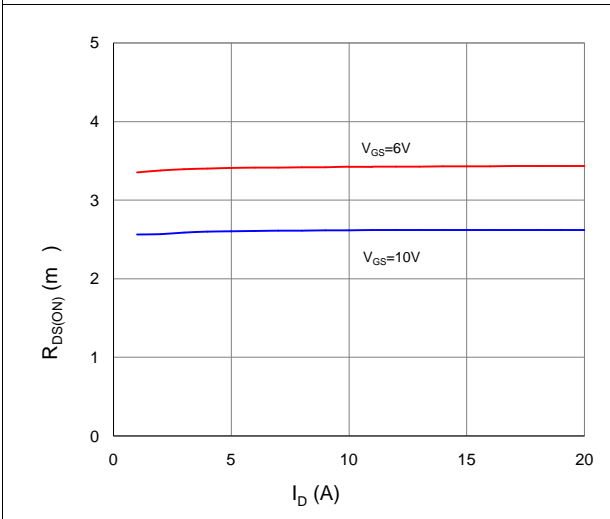


Figure 4. Normalized On-Resistance vs. Junction Temperature

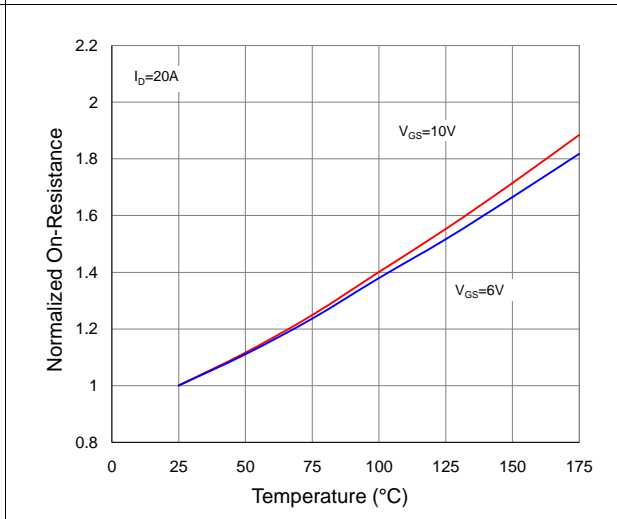


Figure 5. Typical Transfer Characteristics

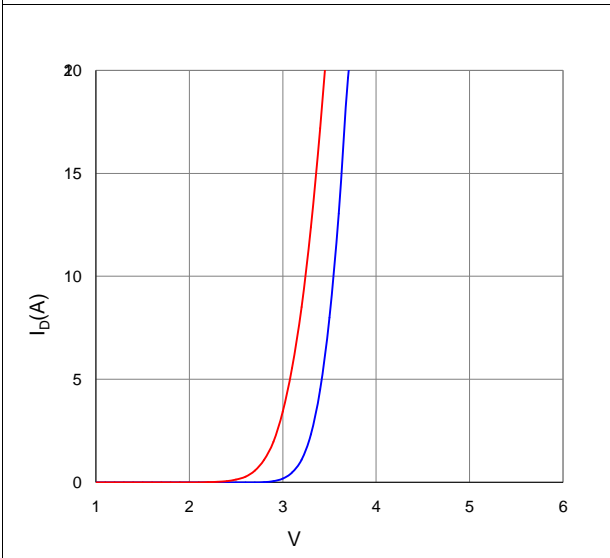


Figure 6. Typical Source-Drain Diode Forward Voltage

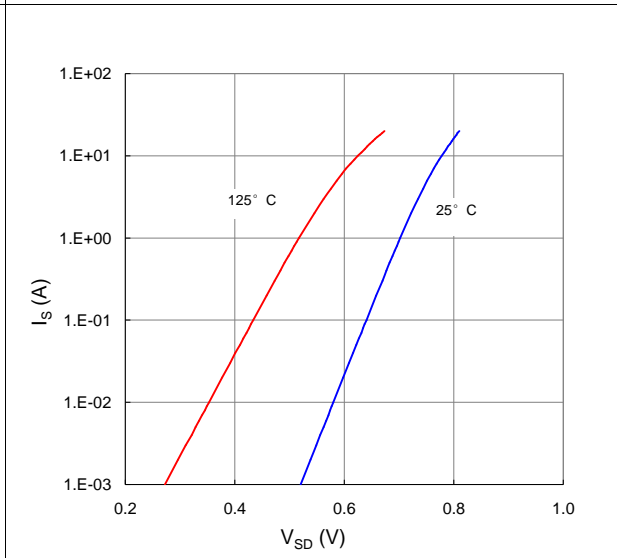


Figure 7. Typical Gate-Charge vs. Gate-to-Source Voltage

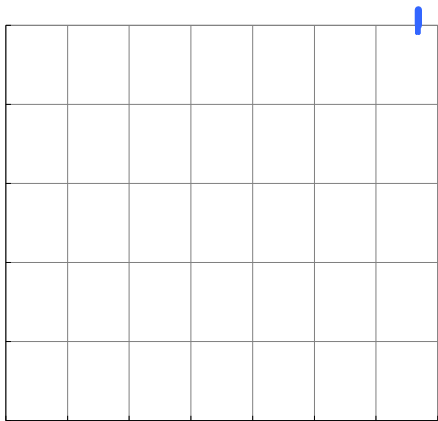


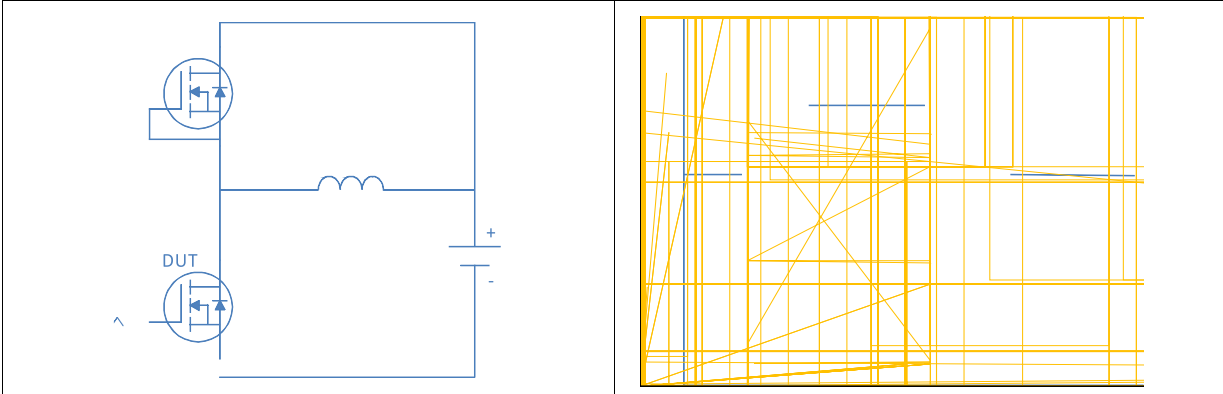
Figure 8. Typical Capacitance vs. Drain-to-Source Voltage

Figure 9. Maximum Safe Operating Area

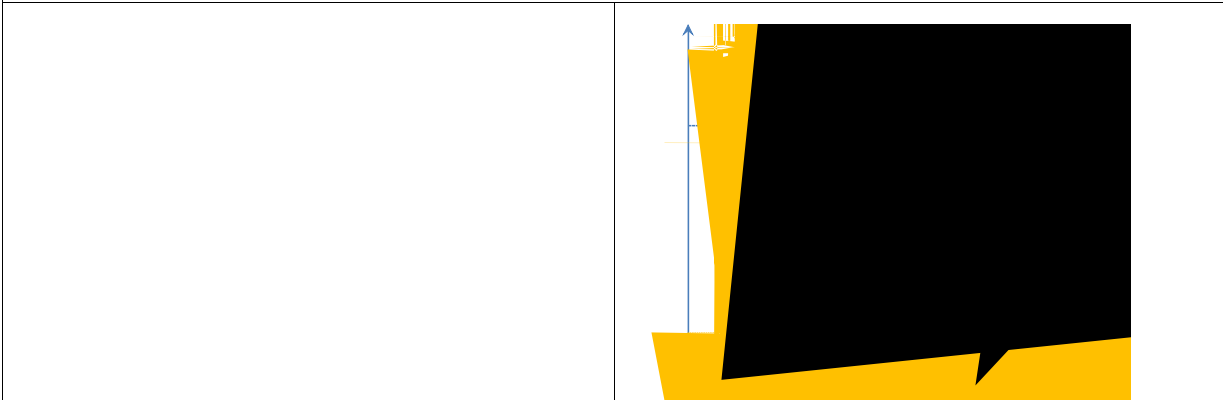
Figure 10. Maximum Drain Current vs. Case Temperature

Figure 11. Normalized Maximum Transient Thermal Impedance, Junction-to-Ambient

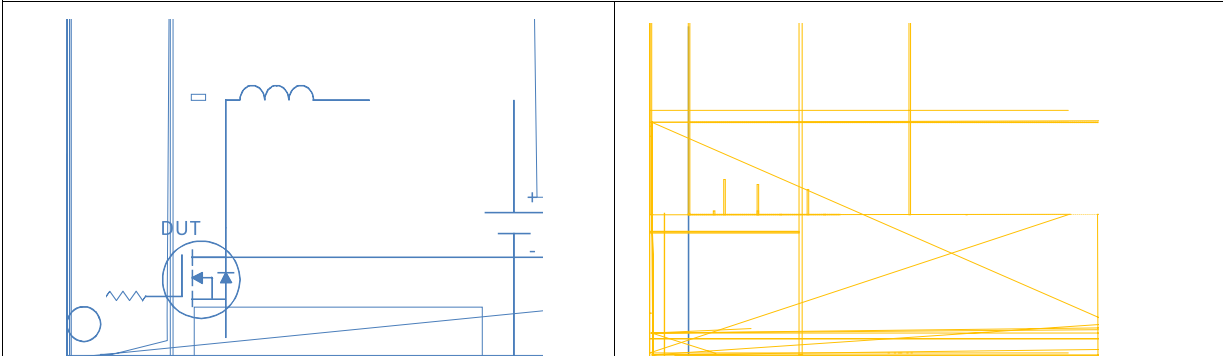
Inductive switching Test



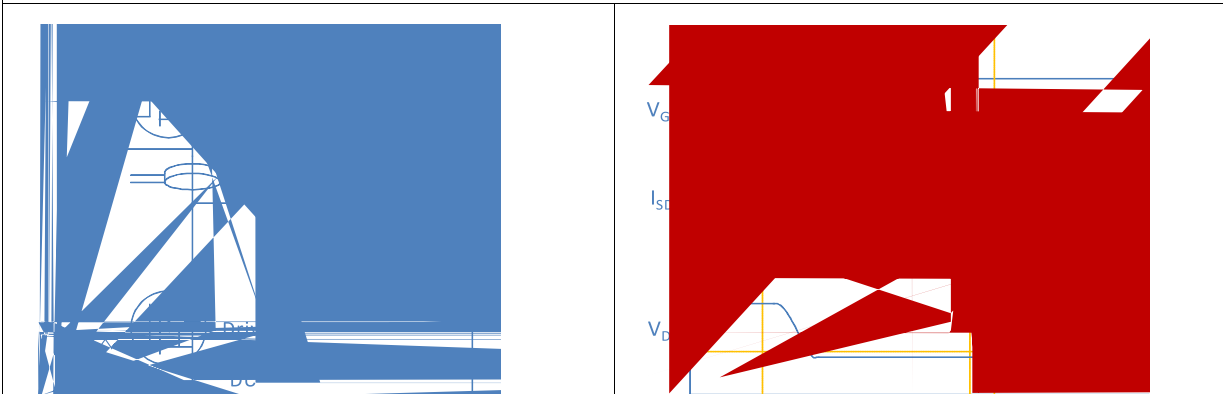
Gate Charge Test



Uclamped Inductive Switching (UIS) Test

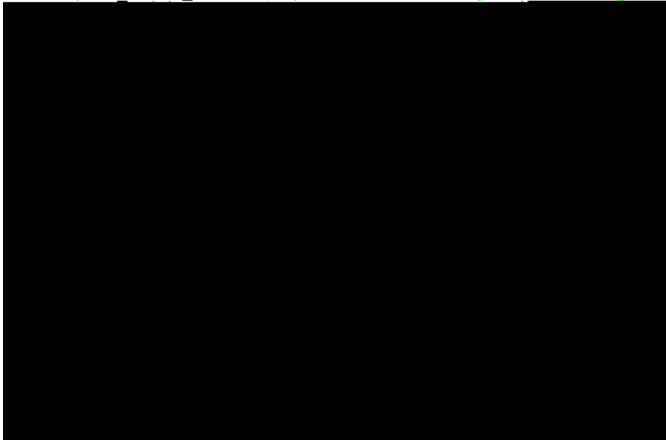


Diode Recovery Test



Package Outline

TO-252, 3 leads



SYMBOL	DIMENSIONAL REQMTS		
	MIN	NOM	MAX
E	6.40	6.60	6.731
L	1.40	1.52	1.77
L1	2.743 REF		
L2	0.508 BSC		
L3	0.89	--	1.27
L4	0.64	--	1.01
L5	--	--	--
D	6.00	6.10	6.223

